

Radiation-induced photoluminescent colour centres in lithium fluoride films for the detection of monochromatic hard X-rays

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Outline

➤ *Introduction*

Lithium fluoride: material properties and main colour centres;
Thermally-evaporated LiF film-based detectors;
LiF radiation imaging detectors: peculiarities.

➤ *LiF film-based detectors irradiated with 7 keV X-rays*

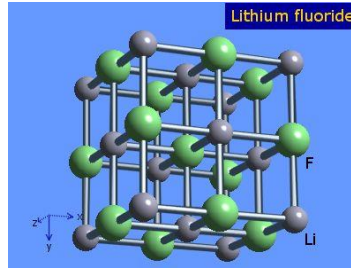
Photoluminescence response of irradiated LiF films grown on glass and Si(100) substrates;
Substrate-enhanced photoluminescence of radiation-induced colour centres;
Edge-enhancement X-ray imaging experiments.

➤ *Conclusions and future perspectives*

Lithium fluoride

Properties and colour centres:

- fcc ionic crystal;
- hard;
- almost non-hygroscopic;
- optically transparent from 120 nm to $7\mu\text{m}$ (band gap ~ 14 eV);
- irradiation by ionising radiations (X rays, γ rays, neutrons, protons etc.) gives rise to stable formation at room temperature (RT) of primary and aggregate colour centres (CCs) characterized by wide tunability and high emission quantum efficiency, even at RT;
- LiF is a nearly tissue-equivalent material ($Z_{\text{eff}} = 8.1$, $Z_{\text{eff water}} = 7.5$)



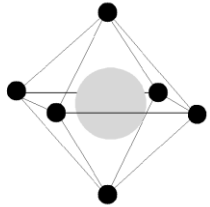
Main applications:

- solid state tuneable lasers (Vis, NIR);
- miniaturized light sources;
- radiation detectors;
- doseimeters.

Nearest neighbour distance (Å)	2.013
Melting point (°C)	848.2
Density (g/cm ³ a RT)	2.639
Molecular weight	25.939
Refractive index at 640 nm, RT	1.3912
Solubility (g/100 g H ₂ O a RT)	0.134
Hardness (Knoop)	102

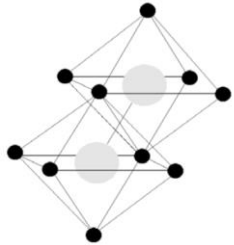
Main physical LiF parameters

Main colour centres in LiF



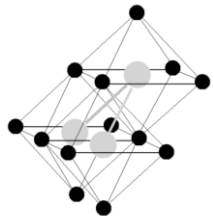
F

F centre is an anion vacancy occupied by an electron.



F₂

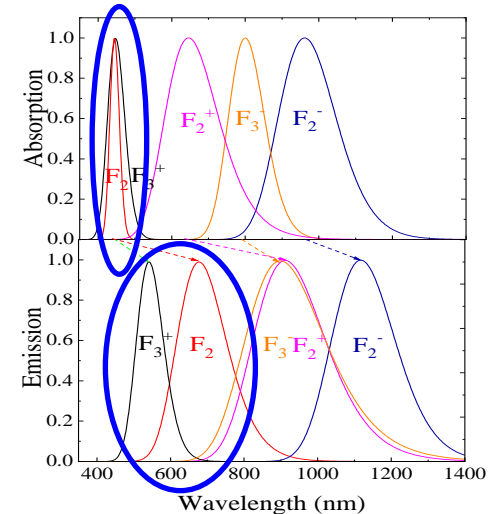
F₂ electronic defect consists of two nearest-neighbour F centres along a $\langle 100 \rangle$ direction of the cubic lattice.



F₃

F₃ centre consists of three F centres in nearest-neighbour sites in the (111) plane.

Center	E _a (eV, nm)	E _e (eV, nm)	FWHM _a (eV)	FWHM _e (eV)
F	5.00, 248	-	0.76	
F₂	2.79, 444	1.83, 678	0.16	0.36
F₃⁺	2.77, 448	2.29, 541	0.29	0.31

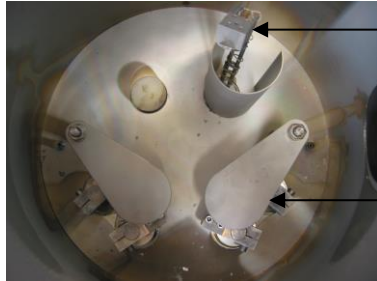


Thermally-evaporated LiF thin films

Optically-transparent polycrystalline LiF films can be grown by thermal evaporation on different substrates, in controlled conditions, tailoring the appropriate geometry, size and thickness.

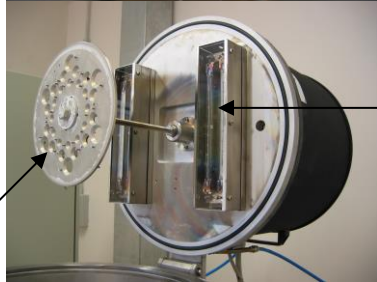


substrate holder

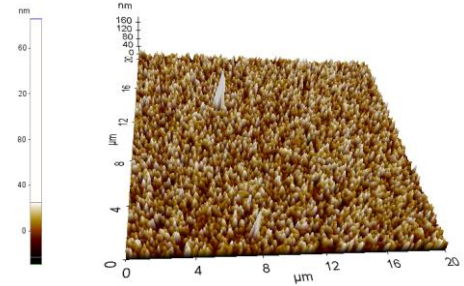
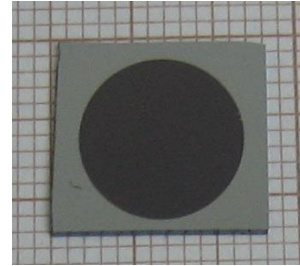


INFICON crystal sensor

shutter



four halogen lamps



1 μm thick LiF film grown on Si(100) substrate and its 3D AFM image

Controlled deposition parameters

- ✓ pressure < 1 mPa;
- ✓ deposition rate: $0.5 \div 2$ nm/s;
- ✓ film thickness: up to few μm
- ✓ substrate temperature: $30 \div 350$ °C
- ✓ nature of substrate: glass, silica, LiF crystals, Si, plastic and metal layers, etc.

GP20 deposition system, ENEA C.R. Frascati.

LiF radiation imaging detectors

They are based on **optical reading** of **F₂** and **F₃⁺** **photoluminescence**.

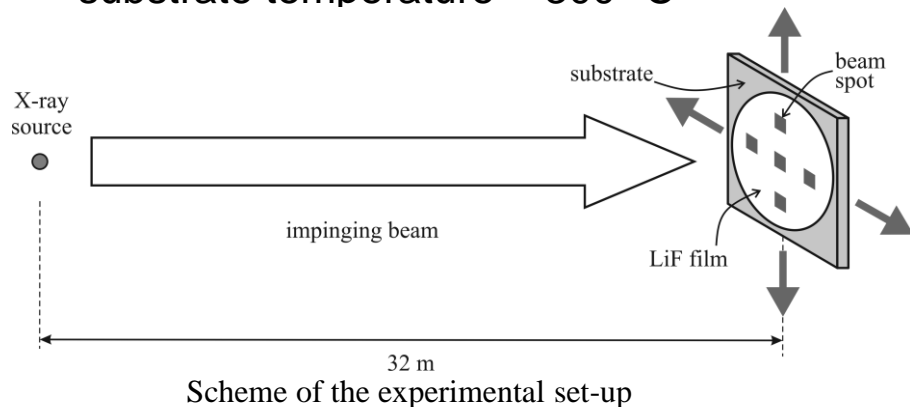
Main features:

- ✓ **multi-purpose** (X-rays, protons, neutrons, electrons, etc.)
- ✓ **easy handling** (insensitive to light, no development needs)
- ✓ **efficient optical readout process** (Vis spectral range)
- ✓ **fast evaluation time** (seconds)
- ✓ **wide dynamic range** ($> 10^5$)
- ✓ **high spatial resolution** (intrinsic < 2 nm, standard < 250 nm)
- ✓ **large field of view** (> 1 cm²)
- ✓ **PL signal stability** (signal stability at RT, multiple evaluations without signal loss)
- ✓ **reusability** (after thermal annealing process).

X-rays irradiation conditions and samples

Detectors:

- ✓ LiF thin films on glass and Si(100) substrates
- ✓ thickness = 0.5, 1.1 and 1.8 μm
- ✓ substrate temperature = 300 $^{\circ}\text{C}$



- X-ray beam energy = 7 keV
- Beam transverse area $\sim (2 \times 2) \text{ mm}^2$
- Dose range = $(13 \div 4.5 \times 10^3) \text{ Gy}$
- X-ray depth of attenuation in LiF $\sim 220 \mu\text{m}$

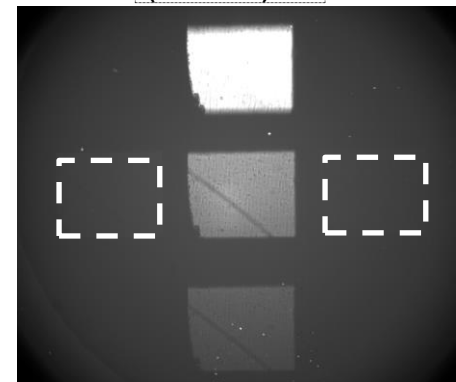
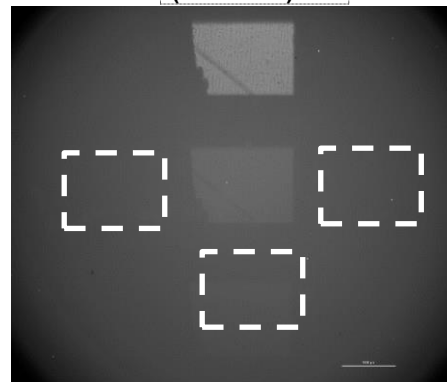


METROLOGIE beamline



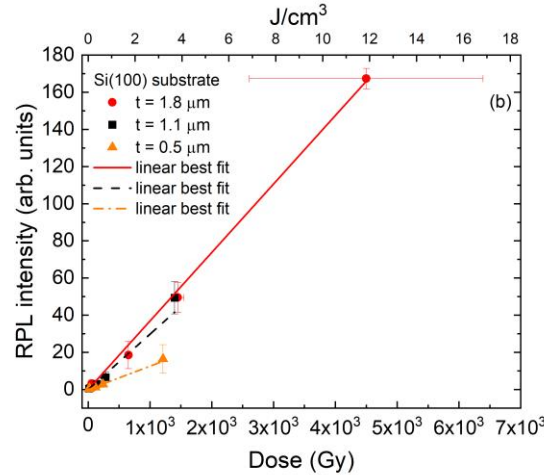
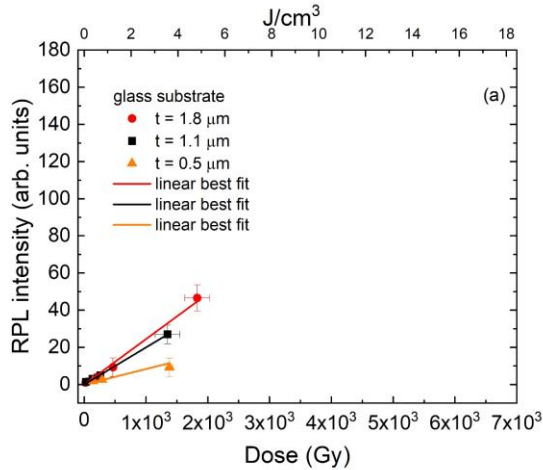
Dose (Gy)
26.9 ± 0.5
51.7 ± 0.3
208 ± 9
467 ± 30
$(1.83 \pm 0.20) \times 10^3$

Dose (Gy)
83.3 ± 0.3
156.8 ± 0.7
652 ± 25
$(1.45 \pm 0.10) \times 10^3$
$(4.50 \pm 1.89) \times 10^3$



Fluorescence images of the thickest LiF films ($t = 1.8 \mu\text{m}$) grown on glass (left) and Si(100) (right) substrates irradiated with monochromatic 7 keV X-rays at five doses.

Spectrally-integrated PL vs Dose

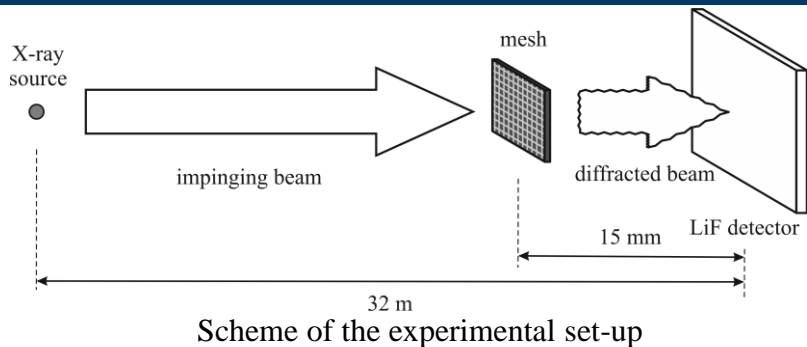


PL response vs. Dose of LiF film detectors grown on glass (a) and Si(100) (b) substrates irradiated with monochromatic 7 keV X-rays, together with their linear best fit.

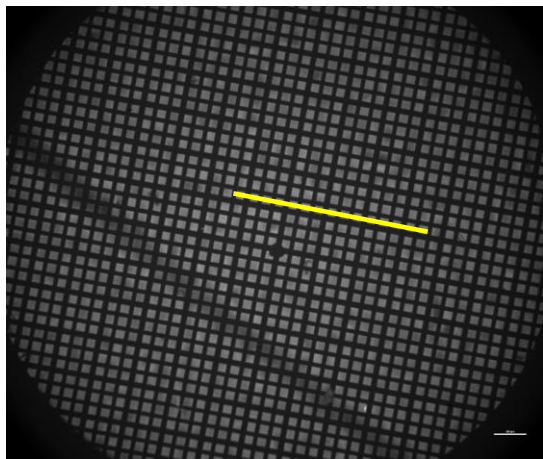
- ✓ The PL response of LiF film detectors linearly depends on the irradiation dose in the investigated dose range;
- ✓ At the same irradiation dose, the PL intensity increases with the film thickness;
- ✓ Lowest detected dose = 13 Gy, delivered to the thinnest LiF film;
- ✓ The ratios of the slopes of the best-fit straight lines for the films grown on Si(100) to those on glass in the same deposition run is ~ 1.5 . This corresponds to a PL enhancement of about 50%, due to the reflectivity of the silicon substrate in the visible spectral range, where the absorption and emission bands of the F_2 and F_3^+ CCs are located.

M.A. Vincenti et al., *ECS Journal of Solid State Science and Technology*, 2023 12 066008

Edge-enhancement X-ray imaging experiments

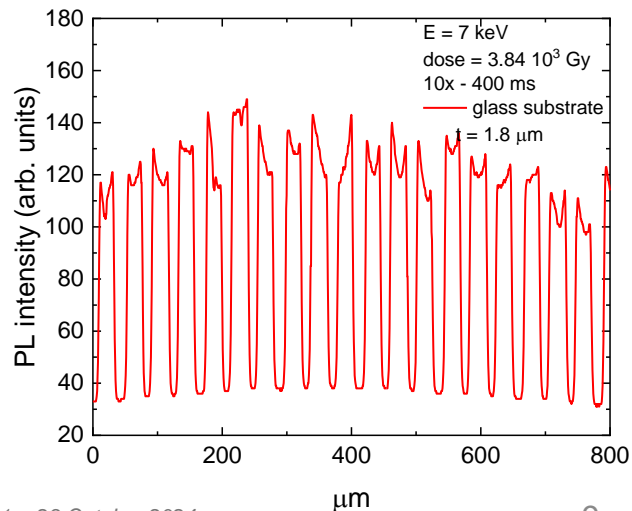


METROLOGIE beamline

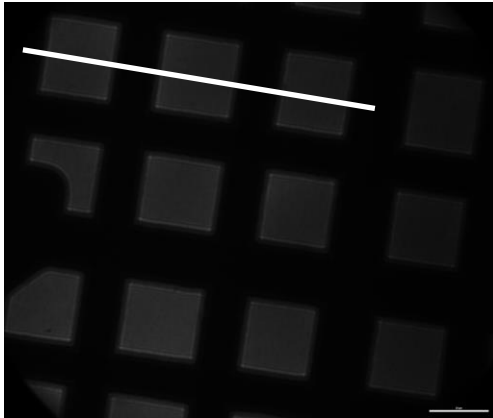


Fluorescence image of the test mesh stored in the LiF film grown on glass, thickness $1.8 \mu\text{m}$, dose $\sim 4 \times 10^3 \text{ Gy}$ (objective magnification 10x, bar size $100 \mu\text{m}$).

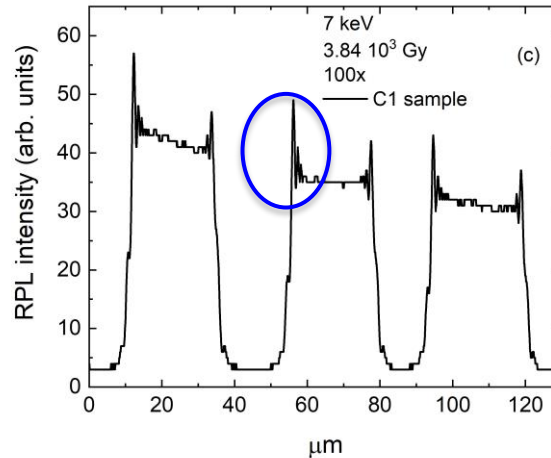
Mesh pitch $\sim 41 \mu\text{m}$



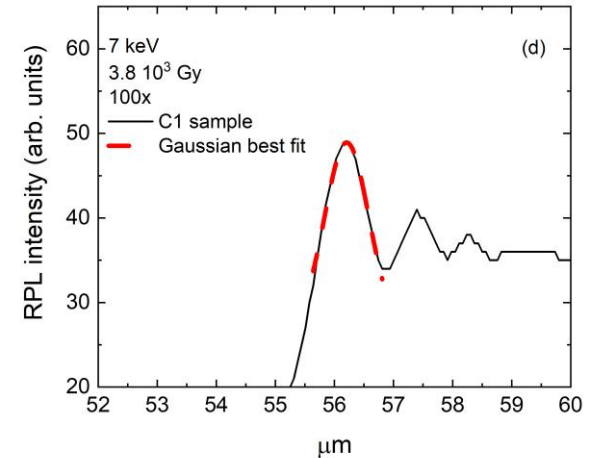
Spatial resolution of LiF detectors



Fluorescence image of the Au mesh stored in the 1.8 μm thick LiF film grown on glass irradiated with 7 keV X-rays, dose = 3.8×10^3 Gy (objective magnification 100 \times , bar size = 20 μm)



PL intensity profile measured along the white line



PL intensity profile of a left portion of the second fluorescent spot together with the Gaussian best fit (red dashed line) of the highest peak of the diffraction pattern.

Half Width at Half Maximum = $(0.38 \pm 0.05) \mu\text{m}$

Conclusions and future perspectives

- ✓ The PL response of LiF film-based detectors of increasing thicknesses, irradiated with 7 keV X-rays at different doses, was measured using a fluorescence microscope.
- ✓ The PL response shows a linear behavior in the investigated dose range ($13 \div 4.5 \times 10^3$ Gy) both for LiF films grown on glass and Si(100) substrate.
- ✓ The lowest detected dose was of 13 Gy.
- ✓ A substrate-enhanced PL response amplified by 50% was obtained for LiF film detectors grown on Si(100) with respect to those deposited on glass in the same deposition run.
- ✓ In edge-enhancement imaging experiments, a submicrometric ($< 0.5 \mu\text{m}$) spatial resolution was obtained on a large field of view ($> 1 \text{ cm}^2$).
- ✓ Further experiments with monochromatic X-rays at energies of several keV are under way to study the LiF film sensitivity and their RPL dose response and improve the reproducibility of the observed behavior by a careful control of the film growth conditions.

Thanks for your attention!

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This research is partially carried out within the TECHEA - Technologies for Health ENEA project.

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